

# JOURNAL OF THE **ELECTRON DEVICES SOCIETY**

## OPEN ACCESS

January 2016 Volume 4 Number 1 IJEDAC (ISSN 2168-6734)

### *Compound Semiconductor Devices*

- 1 High-Current Submicrometer Tri-Gate GaN High-Electron Mobility Transistors With Binary and Quaternary Barriers**

*E. Ture, P. Brückner, B.-J. Godejohann, R. Aidam, M. Alsharif, R. Granzner, F. Schwierz, R. Quay, and O. Ambacher*

### *Thin Film Transistors*

- 7 Abnormal Output Characteristics of p-Type Low Temperature Polycrystalline Silicon Thin Film Transistor Fabricated on Polyimide Substrate**

*S.-W. Lee, C. B. Park, P. J. Jeon, S.-W. Min, J. Y. Lim, H. S. Lee, J.-S. Yoo, S. S. Yoo, and S. Im*

---

**AN IEEE OPEN ACCESS JOURNAL**

---



*Materials, Processing, Packaging*

**11 Threshold Switching Characteristics of Nb/NbO<sub>2</sub>/TiN Vertical Devices**

*Y. Wang, R. B. Comes, S. A. Wolf, and J. Lu*

*Solid State Device Phenomena*

**15 Impact of Hot Carrier Aging on Random Telegraph Noise and Within a Device Fluctuation**

*A. B. Manut, J. F. Zhang, M. Duan, Z. Ji, W. D. Zhang, B. Kaczer, T. Schram, N. Horiguchi, and G. Groeseneken*

*Emerging Technologies and Devices*

**22 Transparent and Flexible Thin Film Electroluminescent Devices Using HiTUS Deposition and Laser Processing Fabrication**

*C. Tsakonas, S. Wakeham, W. M. Cranton, M. Thwaites, G. Boutaud, C. Farrow, D. C. Koutsogeorgis, and R. Ranson*

**30 All-Graphene Planar Double-Quantum-Dot Resonant Tunneling Diodes**

*F. Al-Dirini, M. A. Mohammed, F. M. Hossain, T. Nirmalathas, and E. Skafidas*